

PTO/SB/08A (10-01)

Approved for use through 10/31/2002 OMB 0651-0031

U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/076,486
		Filing Date	February 19, 2002
		First Named Inventor	Stephen L. Casper
		Art Unit	2818
		Examiner Name	M. Tran
Sheet 1 of 4	Attorney Docket Number	M4065.0479/P479	

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No	Document Number Number-Kind Code ² (# known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	class	sub Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
MT	AA	6,469,364	10/2002	Kozicki	257	529
	AB	2002/0168820 App.	11/2002	Kozicki		
	AC	2000/0072188 App.	6/2002	Gilton		
	AD	2002/0123169 App.	9/2002	Moore et al.		
	AE	2002/0123248 App.	9/2002	Moore et al.		
	AF	3,622,319	11/1971	Sharp	430	396
MT	AG	3,743,847	7/1973	Boland	250	505.1
	AH	4,269,935	5/1981	Masters et al.	430	323
	AI	4,312,938	1/1982	Drexler, et al.	430	496
	AJ	4,316,946	1/1982	Masters, et al.	430	9
	AK	4,320,191	3/1982	Yoshikawa et al.	430	296
	AL	4,405,710	9/1983	Balasubramanyam et al.	430	311
	AM	4,419,421	12/1983	Wichelhaus, et al.	429	323
	AN	4,795,657	1/1989	Formigoni et al.	427	96
MT	AO	4,847,674	7/1989	Sliwa et al.	257	767
	AP	4,499,557	2/1985	Holmberg et al.	365	163
	AQ	5,177,567	1/1993	Klersy et al.	257	4
	AR	5,219,788	6/1993	Abernathey et al.	438	636
	AS	5,238,862	8/1993	Blalock et al.	438	398
	AT	5,315,131	5/1994	Kishimoto et al.	257	57
	AU	5,350,484	9/1994	Gardner et al.	438	669
	AV	5,360,981	11/1994	Owen et al.	257	4
MT	AW	5,512,328	4/1996	Yoshimura et al.	427	498
	AX	5,512,773	4/1996	Wolf et al.	257	471
	AY	5,726,083	3/1998	Takaishi	438	210
	AA1	5,841,150	11/1998	Gonzalez et al.	257	3
	AB1	5,846,889	12/1998	Harbison et al.	501	40
	AC1	5,920,788	7/1999	Reinberg	438	466
	AD1	5,998,066	12/1999	Block et al.	430	5
	AE1	6,077,729	6/2000	Harshfield	438	128
MT	AF1	6,117,720	9/2000	Harshfield	438	238
	AG1	6,143,604	11/2000	Chiang et al.	438	253
	AH1	6,177,338	1/2001	Liaw et al.	438	629
	AI1	6,236,059	5/2001	Wolstenholme et al.	257	3
	AJ1	6,297,170	10/2001	Gabriel et al.	438	738
	AK1	6,300,684	10/2001	Gonzalez et al.	257	774
	AL1	6,316,784	11/2001	Zahorik et al.	257	3
MT	AM1	6,329,606	12/2001	Freyman et al.	174	260
	AN1	6,350,679	2/2002	McDaniel et al.	438	634
	AO1	6,376,284	4/2002	Gonzalez et al.	438	129
	AP1	6,391,688	5/2002	Gonzalez et al.	438	128
	AQ1	6,414,376	7/2002	Thakur et al.	257	640
	AR1	6,423,628	7/2002	Li et al.	438	622
	AS1	6,487,106	11/26/2002	Kozicki	365	153
MT	AT1	5,314,772	5/24/1994	Kozicki		

1578618 v1 X%2\$011 DOC

M. TRAN 11/10/03



PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

U. S. Patent and Trademark Office U. S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	10/076,486
				Filing Date	February 19, 2002
				First Named Inventor	Stephen L. Casper
				Art Unit	2818
				Examiner Name	M. Tran
Sheet	2	of	4	Attorney Docket Number	M4065.0479/P479

AT	AU1	2002/0190350 APP	12/19/2002	Kozicki		
	AV1	2003/0027416 APP	2/6/2003	Moore		
	AW1	2003/0001229 APP	1/2/2003	Moore et al.		
	AX1	2002/0106849 APP	8/8/2002	Moore		
	AY1	2002/0127886 APP	9/12/2002	Moore et al.		
	AZ1	2002/0123170 APP	9/5/2002	Moore et al.		
	BA1	2002/0163828 APP	11/2002	Krieger et al.		
	BB1	6,072,716	6/2000	Jacobson et al.	365	163
	BC1	5,272,359	12/93	Nagasubramanian et al.	257	40
	BD1	4,671,618	6/87	Wu et al.	349	92
	BE1	4,800,526	1/89	Lewis	365	118
	BF1	2003/0035314	02/20/03	Kozicki		
	BG1	2003/0035315	02/20/03	Kozicki		
	BH1	6,314,014	11/6/01	Lowrey et al.	365	100
	BI1	5,883,827	3/16/99	Morgan	365	100
W	BJ1	4,112,512	9/5/78	Arzubi et al.	365	149

M. TRAN

11/11/03



PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

U. S. Patent and Trademark Office U. S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO		Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/076,486		
		Filing Date	February 19, 2002		
		First Named Inventor	Stephen L. Casper		
		Art Unit	2818		
		Examiner Name	M. Tran		
Sheet	3	of	4	Attorney Docket Number	M4065.0479/P479

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
My	BA	JP 56126916	10/1981	Akira et al.		
	BB					

Examiner Signature	M. TRAN	Date Considered	11/12/03
-----------------------	---------	--------------------	----------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

PTO/SB/08B (10-01)

Approved for use through 10/31/2002.OMB 0651-0031

U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	10/076,486
				Filing Date	February 19, 2002
				First Named Inventor	Stephen L. Casper et al.
				Group Art Unit	2818
				Examiner Name	M. Tran
				Attorney Docket Number	M4065.0479/P479
Sheet	4	of	4		

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
AY	CA	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: <i>Programmable Metalization Cell(PMC)</i> , pp 1-6 (Pre-May 2000).	
	CB	Helbert et al., <i>Intralevel hybnd resist process with submicron capability</i> SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 24-29 (1982).	
	CC	Hilt, DISSERTATION: <i>Materials characterization of Silver Chalcogenide Programmable Metalization Cells</i> , Arizona State University, pp Title page-114 (UMI Company, May 1999).	
AY	CD	Hirose et al., <i>High Speed Memory Behavior and Reliability of an Amorphous As₂S₃ Film Doped Ag</i> , PHYS. STAT. SOL. (a) 61, pp. 87-90 (1980).	
	CE	Holmquist et al., <i>Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems</i> , 62 J. AMER. CERAM. SOC., No. 3-4, pp. 183-188 (March-April 1979).	
	CF	Huggelt et al., <i>Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF₆</i> , 42 APPL. PHYS. LETT., No. 7, pp. 592-594 (April 1983)	
	CG	Kawaguchi et al., <i>Mechanism of photosurface deposition</i> , 164-166 J. NON-CRYST. SOLIDS, pp. 1231-1234 (1993).	
	CH	Kolobov and Elliott, <i>Photodoping of Amorphous Chalcogenides by Metals</i> , Advances in Physics, Vol. 40, No 5, 625-684 (1991).	
AY	CI	Kozicki, et al., "Applications of Programmable Resistance Changes in Metal-doped Chalcogenides", Proceedings of the 1999 Symposium on Solid State Ionic Devices, Editors - E.D. Wachsman et al., The Electrochemical Society, Inc., 1 - 12 (1999)	
	CJ	Kozicki, et al., <i>Nanoscale effects in devices based on chalcogenide solid solutions</i> , Superlattices and Microstructures, 27, 485-488 (2000).	
	CK	Kozicki, et al., <i>Nanoscale phase separation in Ag-Ge-Se glasses</i> , Microelectronic Engineering, vol. 63/1-3, 155-159 (2002).	
	CL	M.N. Kozicki and M. Mitkova, <i>Silver incorporation in thin films of selenium rich Ge-Se glasses</i> , Proceedings of the XIX International Congress on Glass, Society for Glass Technology, 226-227 (2001).	
AY	CM	McHardy et al., <i>The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation</i> , 20 J. PHYS. C: SOLID STATE PHYS., pp. 4055-4075 (1987)f	
	CN	Owen et al., <i>Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures</i> , NANOSTRUCTURE PHYSICS AND FABRICATION, pp. 447-451 (M. Reed ed. 1989).	
	CO	Shimizu et al., <i>The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses</i> , 46 B. CHEM SOC. JAPAN, No. 12, pp. 3662-3365 (1973).	
	CP	Michael N. Kozicki, <i>1. Programmable Metallization Cell Technology Description</i> , February 18, 2000	
MI	CQ	Michael N. Kozicki, Axon Technologies Corp. and Arizona State University, Presentation to Micron Technology, Inc., April 6, 2000	

Examiner Signature	M. TIAN	Date Considered	11	12	03
-----------------------	---------	--------------------	----	----	----

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional) ²Applicant is to place a check mark here if English language Translation is attached

SEP 22 1971

DECEMBER

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.



Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete If Known

Application Number	10/076,486
Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper
Art Unit	2818
Examiner Name	Not Known
Attorney Docket Number	M4065.0479/P479

Sheet

1

of

8

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Number-Kind Code ² (if known)			Class	Sub
AY	AA	6,388,324	05/14/2002	Kozicki et al.	257	750
	AB	US 2002/0000666	01/03/2002	Kozicki et al.	250	377
	AC	5,500,532	03/19/1996	Kozicki et al.	260	374
	AD	6,418,049	07/09/2002	Kozicki et al.	265	374
	AE	5,751,012	05/12/1998	Wolstenholme et al.	257	5
AY	AF	5,789,277	08/04/1998	Zahorik et al.	438	95
	AG	6,348,365	02/19/2002	Moore et al.	438	130

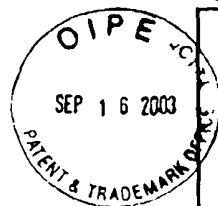
FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
AY	BA	WO 02/21542	03/14/2002	Kozicki et al.		
	BB	WO 00/48196	08/17/2000	Kozicki et al.		
AY	BC	WO 97/48032	12/18/1997	Kozicki et al.		
	BD	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature	M. TRAN	Date Considered	11/12/03
-----------------------	---------	--------------------	----------

*EXAMINER. Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

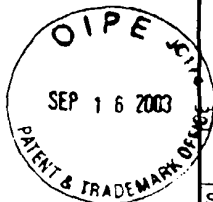


PTO/SB/088 (10-01)
Approved for use through 10/31/2002 OMB 0651-0031
U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO		Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/076,486		
		Filing Date	February 19, 2002		
		First Named Inventor	Stephen L. Casper		
		Group Art Unit	2818		
		Examiner Name	Not Known		
Sheet	2	of	8	Attorney Docket Number	M4065.0479/P479

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
AT	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.	
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge ₂₅ -xSbx, Appl. Phys. A 55 (1992) 167-169.	
df	CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe _{1-x} , Egypt, J. Phys. 17 (1986) 335-342.	
	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
df	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
	CL	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.	
	CM	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029.	
	CN	Belin, R.; Zerouale, A.; Pradel, A.; Ribes, M., Ion dynamics in the argyrodite compound Ag ₇ GeSe ₅ I: non-Arrhenius behavior and complete conductivity spectra, Solid State Ionics 143 (2001) 445-455.	
	CO	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.	
df	CP	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag ₂ Se-M, Thin solid films 70 (1980) L1-L4.	
	CQ	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.	
	CR	Bernede, J.C., Switching and silver movements in Ag ₂ Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.	
	CS	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.	
	CT	Bernede, J.C.; Conan, A.; Fousenan't, E.; El Bouchairi, B.; Goureaux, G., Polarized memory switching effects in Ag ₂ Se/Se/M thin film sandwiches, Thin solid films 97 (1982) 165-171.	
	CU	Bernede, J.C.; Khelil, A.; Kettaf, M.; Conan, A., Transition from S- to N-type differential negative resistance in Al-Al ₂ O ₃ -Ag ₂ -xSe _{1+x} thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.	
	CV	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg ₄ I ₅ , Solid State Ionics 70/71 (1994) 72-76.	
df	CW	Boolchand, P., The maximum in glass transition temperatur (T _g) near x=1/3 in GexSe _{1-x}	

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.



Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	3	of	8
-------	---	----	---

Complete if Known

Application Number	10/076,486
Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper
Group Art Unit	2818
Examiner Name	Not Known
Attorney Docket Number	M4065.0479/P479

✓		Glasses, Asian Journal of Physics (2000) 9, 709-72.	
	CX	Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.	
	CY	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703	
	CZ	Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.	
✓	CA1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.	
	CB1	Boolchand, P.; Grothaus, J.; Bresser, W.J.; Suranyi, P., Structural origin of broken chemical order in a GeSe ₂ glass, Phys. Rev. B 25 (1982) 2975-2978.	
	CC1	Boolchand, P.; Grothaus, J.; Phillips, J.C., Broken chemical order and phase separation in GexSe _{1-x} glasses, Solid state comm. 45 (1983) 183-185.	
	CD1	Boolchand, P.; Bresser, W.J., Compositional trends in glass transition temperature (T _g), network connectivity and nanoscale chemical phase separation in chalcogenides, Dept. of ECECS, Univ. Cincinnati (October 28, 1999) 45221-0030.	
	CE1	Boolchand, P.; Grothaus, J., Molecular Structure of Melt-Quenched GeSe ₂ and GeS ₂ glasses compared, Proc. Int. Conf. Phys. Semicond. (Eds. Chadi and Harrison) 17 th (1985) 833-36.	
✓	CF1	Bresser, W.; Boolchand, P.; Suranyi, P., Rigidity percolation and molecular clustering in network glasses, Phys. Rev. Lett. 56 (1986) 2493-2496.	
	CG1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; de Neufville, J.P., Intrinsically broken chalcogen chemical order in stoichiometric glasses, Journal de Physique 42 (1981) C4-193-C4-196.	
	CH1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; Hernandez, J.G., Molecular phase separation and cluster size in GeSe ₂ glass, Hyperfine Interactions 27 (1986) 389-392.	
	CI1	Cohen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe ₂ Crystals, Science 258 (1992) 271-274.	
	CJ1	Chatterjee, R.; Asokan, S.; Titus, S.S.K., Current-controlled negative-resistance behavior and memory switching in bulk As-Te-Se glasses, J. Phys. D: Appl. Phys. 27 (1994) 2624-2627.	
✓	CK1	Chen, C.H.; Tai, K.L., Whisker growth induced by Ag photodoping in glassy GexSe _{1-x} films, Appl. Phys. Lett. 37 (1980) 1075-1077.	
	CL1	Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936.	
	CM1	Chen, G.; Cheng, J.; Chen, W., Effect of Si ₃ N ₄ on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.	
	CN1	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.	
	CO1	Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786.	
	CP1	Dalven, R.; Gill, R., Electrical properties of beta-Ag ₂ Te and beta-Ag ₂ Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.	
	CQ1	Davis, E.A., Semiconductors without form, Search 1 (1970) 152-155.	
✓	CR1	Dearnaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191.	
	CS1	Dejus, R.J.; Susman, S.; Volin, K.J.; Montague, D.G.; Price, D.L., Structure of Vitreous Ag-Ge-Se, J. Non-Cryst. Solids 143 (1992) 162-180.	
	CT1	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.	
✓	CU1	Drusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous	

M. TRAN

11/13/03

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.



Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete If Known

Application Number	10/076,486
Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper
Group Art Unit	2818
Examiner Name	Not Known
Attorney Docket Number	M4065.0479/P479

Sheet	4	of	8
-------	---	----	---

CV1	silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.
CW1	El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag ₂ -xSe _{1+x} /n-Si diodes, Thin Solid Films 110 (1983) 107-113.
CX1	El Gharras, Z.; Bourahla, A.; Vautier, C., Role of photoinduced defects in amorphous GexSe _{1-x} photoconductivity, J. Non-Cryst. Solids 155 (1993) 171-179.
CY1	El Ghrandi, R.; Calas, J.; Galibert, G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273.
CZ1	El-kady, Y.L., The threshold switching in semiconducting glass Ge ₂₁ Se ₁₇ Te ₆₂ , Indian J. Phys. 70A (1996) 507-516.
CA2	Elliott, S.R., A unified mechanism for metal photodissolution in amorphous chalcogenide materials, J. Non-Cryst. Solids 130 (1991) 85-97.
CB2	Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034.
CC2	Elsamanoudy, M.M.; Hegab, N.A.; Fadel, M., Conduction mechanism in the pre-switching state of thin films containing Te As Ge Si, Vacuum 46 (1995) 701-707.
CD2	El-Zahed, H.; El-Korashy, A., Influence of composition on the electrical and optical properties of Ge ₂₀ BixSe _{80-x} films, Thin Solid Films 376 (2000) 236-240.
CE2	Fadel, M., Switching phenomenon in evaporated Se-Ge-As thin films of amorphous chalcogenide glass, Vacuum 44 (1993) 851-855.
CF2	Fadel, M.; El-Shair, H.T., Electrical, thermal and optical properties of Se ₇₅ Ge ₇ Sb ₁₈ , Vacuum 43 (1992) 253-257.
CG2	Feng, X.; Bresser, W.J.; Boolchand, P., Direct evidence for stiffness threshold in Chalcogenide glasses, Phys. Rev. Lett. 78 (1997) 4422-4425.
CH2	Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, J. Non-Cryst. Solids 222 (1997) 137-143.
CI2	Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe ₂ thin films, Phys. Rev. B 38 (1988) 12388-12403.
CJ2	Fleury, G.; Hamou, A.; Viger, C.; Vautier, C., Conductivity and crystallization of amorphous selenium, Phys. Stat. Sol. (a) 64 (1981) 311-316.
CK2	Fritzsche, H., Optical and electrical energy gaps in amorphous semiconductors, J. Non-Cryst. Solids 6 (1971) 49-71.
CL2	Fritzsche, H., Electronic phenomena in amorphous semiconductors, Annual Review of Materials Science 2 (1972) 697-744.
CM2	Gates, B.; Wu, Y.; Yin, Y.; Yang, P.; Xia, Y., Single-crystalline nanowires of Ag ₂ Se can be synthesized by templating against nanowires of trigonal Se, J. Am. Chem. Soc. (2001) currently ASAP.
CN2	Gosain, D.P.; Nakamura, M.; Shimizu, T.; Suzuki, M.; Okano, S., Nonvolatile memory based on reversible phase transition phenomena in telluride glasses, Jap. J. Appl. Phys. 28 (1989) 1013-1018.
CO2	Guin, J.-P.; Rouxel, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.
CP2	Guin, J.-P.; Rouxel, T.; Sangleboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52.
CQ2	Gupta, Y.P., On electrical switching and memory effects in amorphous chalcogenides, J. Non-Cryst. Sol. 3 (1970) 148-154.

M. TRAN

4/13/07

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete If Known

Application Number	10/076,486
Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper
Group Art Unit	2818
Examiner Name	Not Known
Attorney Docket Number	M4065.0479/P479

Sheet 5 of 8

CR2	Haberland, D.R.; Stiegler, H., New experiments on the charge-controlled switching effect in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 408-414.
CS2	Haifz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses, J. Appl. Phys. 54 (1983) 1950-1954.
CT2	Hajto, J.; Rose, M.J.; Osborne, I.S.; Snell, A.J.; Le Comber, P.G.; Owen, A.E., Quantization effects in metal/a-Si:H/metal devices, Int. J. Electronics 73 (1992) 911-913.
CU2	Hajto, J.; Hu, J.; Snell, A.J.; Turvey, K.; Rose, M., DC and AC measurements on metal/a-Si:H/metal room temperature quantised resistance devices, J. Non-Cryst. Solids 266-269 (2000) 1058-1061.
CV2	Hajto, J.; McAuley, B.; Snell, A.J.; Owen, A.E., Theory of room temperature quantized resistance effects in metal-a-Si:H-metal thin film structures, J. Non-Cryst. Solids 198-200 (1996) 825-828.
CW2	Hajto, J.; Owen, A.E.; Snell, A.J.; Le Comber, P.G.; Rose, M.J., Analogue memory and ballistic electron effects in metal-amorphous silicon structures, Phil. Mag. B 63 (1991) 349-369.
CX2	Hayashi, T.; Ono, Y.; Fukaya, M.; Kan, H., Polarized memory switching in amorphous Se film, Japan. J. Appl. Phys. 13 (1974) 1163-1164.
CY2	Hegab, N.A.; Fadel, M.; Sedeek, K., Memory switching phenomena in thin films of chalcogenide semiconductors, Vacuum 45 (1994) 459-462.
CZ2	Hirose, Y.; Hirose, H., Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As ₂ S ₃ films, J. Appl. Phys. 47 (1976) 2767-2772.
CA3	Hong, K.S.; Speyer, R.F., Switching behavior in II-IV-V ₂ amorphous semiconductor systems, J. Non-Cryst. Solids 116 (1990) 191-200.
CB3	Hosokawa, S., Atomic and electronic structures of glassy GexSe1-x around the stiffness threshold composition, J. Optoelectronics and Advanced Materials 3 (2001) 199-214.
CC3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Constant current forming in Cr/p+a-Si:H/V thin film devices, J. Non-Cryst. Solids 227-230 (1998) 1187-1191.
CD3	Hu, J.; Hajto, J.; Snell, A.J.; Owen, A.E.; Rose, M.J., Capacitance anomaly near the metal-non-metal transition in Cr-hydrogenated amorphous Si-V thin-film devices, Phil. Mag. B. 74 (1996) 37-50.
CE3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Current-induced instability in Cr-p+a-Si:H-V thin film devices, Phil. Mag. B 80 (2000) 29-43.
CF3	Iizima, S.; Sugi, M.; Kikuchi, M.; Tanaka, K., Electrical and thermal properties of semiconducting glasses As-Te-Ge, Solid State Comm. 8 (1970) 153-155.
CG3	Ishikawa, R.; Kikuchi, M., Photovoltaic study on the photo-enhanced diffusion of Ag in amorphous films of Ge ₂ S ₃ , J. Non-Cryst. Solids 35 & 36 (1980) 1061-1066.
CH3	Iyetomi, H.; Vashishta, P.; Kalia, R.K., Incipient phase separation in Ag/Ge/Se glasses: clustering of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142.
CI3	Jones, G.; Collins, R.A., Switching properties of thin selenium films under pulsed bias, Thin Solid Films 40 (1977) L15-L18.
CJ3	Joullie, A.M.; Marucchi, J., On the DC electrical conduction of amorphous As ₂ Se ₇ before switching, Phys. Stat. Sol. (a) 13 (1972) K105-K109.
CK3	Joullie, A.M.; Marucchi, J., Electrical properties of the amorphous alloy As ₂ Se ₅ , Mat. Res. Bull. 8 (1973) 433-442.
CL3	Kaplan, T.; Adler, D., Electrothermal switching in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 538-543.
CM3	Kawaguchi, T.; Maruno, S.; Elliott, S.R., Optical, electrical, and structural properties of amorphous Ag-Ge-S and Ag-Ge-Se films and comparison of photoinduced and thermally induced phenomena of both systems, J. Appl. Phys. 79 (1996) 9096-9104.
CN3	Kawaguchi, T.; Masui, K., Analysis of change in optical transmission spectra resulting from Ag photodoping in chalcogenide film, Japn. J. Appl. Phys. 26 (1987) 15-21.

M. TRAN

11/14/03

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	6	of	8	Complete If Known
-------	---	----	---	-------------------

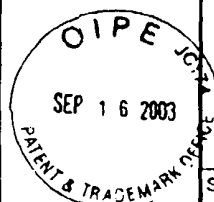
Application Number	10/076,486
Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper
Group Art Unit	2818
Examiner Name	Not Known
Attorney Docket Number	M4065.0479/P479

CO3	Kawasaki, M.; Kawamura, J.; Nakamura, Y.; Aniya, M., Ionic conductivity of $\text{Ag}_x(\text{GeSe}_3)_{1-x}$ ($0 < x \leq 0.571$) glasses, Solid state Ionics 123 (1999) 259-269.
CP3	Kluge, G.; Thomas, A.; Klabes, R.; Grotzschel, R., Silver photodiffusion in amorphous GeSe_{100-x} , J. Non-Cryst. Solids 124 (1990) 186-193.
CQ3	Kolobov, A.V., On the origin of p-type conductivity in amorphous chalcogenides, J. Non-Cryst. Solids 198-200 (1996) 728-731.
CR3	Kolobov, A.V., Lateral diffusion of silver in vitreous chalcogenide films, J. Non-Cryst. Solids 137-138 (1991) 1027-1030.
CS3	Korkinova, Ts.N.; Andreichin, R.E., Chalcogenide glass polarization and the type of contacts, J. Non-Cryst. Solids 194 (1996) 256-259.
CT3	Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTi chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.
CU3	Lakshminarayan, K.N.; Srivastava, K.K.; Panwar, O.S.; Dumar, A., Amorphous semiconductor devices: memory and switching mechanism, J. Instn Electronics & Telecom. Engrs 27 (1981) 16-19.
CV3	Lal, M.; Goyal, N., Chemical bond approach to study the memory and threshold switching chalcogenide glasses, Indian Journal of pure & appl. phys. 29 (1991) 303-304.
CW3	Leimer, F.; Stotzel, H.; Kottwitz, A., Isothermal electrical polarisation of amorphous GeSe films with blocking Al contacts influenced by Poole-Frenkel conduction, Phys. Stat. Sol. (a) 29 (1975) K129-K132.
CX3	Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GeSe_{1-x} glass, Appl. Phys. Lett. 46 (1985) 543-545.
CY3	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on Se-SnO_2 system, Jap. J. Appl. Phys. 11 (1972) 1657-1662.
CZ3	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on amorphous selenium thin films, Jpn. J. Appl. Phys. 11 (1972) 606.
CA4	Mazurier, F.; Levy, M.; Souquet, J.L., Reversible and irreversible electrical switching in $\text{TeO}_2\text{-V}_2\text{O}_5$ based glasses, Journal de Physique IV 2 (1992) C2-185 - C2-188.
CB4	Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures ($\text{M}=\text{Ni, Bi}$), Mat. Chem. And Phys. 28 (1991) 253-258.
CC4	Mitkova, M.; Boolchand, P., Microscopic origin of the glass forming tendency in chalcogenides and constraint theory, J. Non-Cryst. Solids 240 (1998) 1-21.
CD4	Mitkova, M.; Kozicki, M.N., Silver incorporation in Ge-Se glasses used in programmable metallization cell devices, J. Non-Cryst. Solids 299-302 (2002) 1023-1027.
CE4	Mitkova, M.; Wang, Y.; Boolchand, P., Dual chemical role of Ag as an additive in chalcogenide glasses, Phys. Rev. Lett. 83 (1999) 3848-3851.
CF4	Miyatani, S.-y., Electronic and ionic conduction in $(\text{AgxCu}_{1-x})_2\text{Se}$, J. Phys. Soc. Japan 34 (1973) 423-432.
CG4	Miyatani, S.-y., Electrical properties of Ag_2Se , J. Phys. Soc. Japan 13 (1958) 317.
CH4	Miyatani, S.-y., Ionic conduction in beta- Ag_2Te and beta- Ag_2Se , Journal Phys. Soc. Japan 14 (1959) 996-1002.
CI4	Mott, N.F., Conduction in glasses containing transition metal ions, J. Non-Cryst. Solids 1 (1968) 1-17.
CJ4	Nakayama, K.; Kitagawa, T.; Ohmura, M.; Suzuki, M., Nonvolatile memory based on phase transitions in chalcogenide thin films, Jpn. J. Appl. Phys. 32 (1993) 564-569.
CK4	Nakayama, K.; Kojima, K.; Hayakawa, F.; Imai, Y.; Kitagawa, A.; Suzuki, M., Submicron nonvolatile memory cell based on reversible phase transition in chalcogenide glasses, Jpn. J. Appl. Phys. 39 (2000) 6157-6161.
CL4	Nang, T.T.; Okuda, M.; Matsushita, T.; Yokota, S.; Suzuki, A., Electrical and optical parameters of GeSe_{1-x} amorphous thin films, Jap. J. App. Phys. 15 (1976) 849-853.
CM4	Narayanan, R.A.; Asokan, S.; Kumar, A., Evidence concerning the effect of topology on

M. TRAN

11/14/03

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number



Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	7	of	8
-------	---	----	---

Complete If Known

Application Number	10/076,486
Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper
Group Art Unit	2818
Examiner Name	Not Known
Attorney Docket Number	M4065.0479/P479

		electrical switching in chalcogenide network glasses, Phys. Rev. B 54 (1996) 4413-4415.	
AT	CN4	Neale, R.G.; Aseltine, J.A., The application of amorphous materials to computer memories, IEEE transactions on electron dev. Ed-20 (1973) 195-209.	
	CO4	Ovshinsky S.R.; Fritzsche, H., Reversible structural transformations in amorphous semiconductors for memory and logic, Metallurgical transactions 2 (1971) 641-645.	
	CP4	Ovshinsky, S.R., Reversible electrical switching phenomena in disordered structures, Phys. Rev. Lett. 21 (1968) 1450-1453.	
	CQ4	Owen, A.E.; LeComber, P.G.; Sarabayrouse, G.; Spear, W.E., New amorphous-silicon electrically programmable nonvolatile switching device, IEE Proc. 129 (1982) 51-54	
AT	CR4	Owen, A.E.; Firth, A.P.; Ewen, P.J.S., Photo-induced structural and physico-chemical changes in amorphous chalcogenide semiconductors, Phil. Mag. B 52 (1985) 347-362.	
	CS4	Owen, A.E.; LeComber, P.G.; Hajto, J.; Rose, M.J.; Snell, A.J., Switching in amorphous devices, Int. J. Electronics 73 (1992) 897-906.	
	CT4	Pearson, A.D.; Miller, C.E., Filamentary conduction in semiconducting glass diodes, App. Phys. Lett. 14 (1969) 280-282.	
	CU4	Pinto, R.; Ramanathan, K.V., Electric field induced memory switching in thin films of the chalcogenide system Ge-As-Se, Appl. Phys. Lett. 19 (1971) 221-223.	
	CV4	Popescu, C., The effect of local non-uniformities on thermal switching and high field behavior of structures with chalcogenide glasses, Solid-state electronics 18 (1975) 671-681.	
AT	CW4	Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537.	
	CX4	Popov, A.I.; Geller, I.KH.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.	
	CY4	Prakash, S.; Asokan, S.; Ghare, D.B., Easily reversible memory switching in Ge-As-Te glasses, J. Phys. D: Appl. Phys. 29 (1996) 2004-2008.	
	CZ4	Rahman, S.; Sivarama Sastry, G., Electronic switching in Ge-Bi-Se-Te glasses, Mat. Sci. and Eng. B12 (1992) 219-222.	
	CA5	Ramesh, K.; Asokan, S.; Sangunni, K.S.; Gopal, E.S.R., Electrical Switching in germanium telluride glasses doped with Cu and Ag, Appl. Phys. A 69 (1999) 421-425.	
AT	CB5	Rose, M.J.; Hajto, J.; Lecomber, P.G.; Gage, S.M.; Choi, W.K.; Snell, A.J.; Owen, A.E., Amorphous silicon analogue memory devices, J. Non-Cryst. Solids 115 (1989) 168-170.	
	CC5	Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a-Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080.	
	CD5	Schuocker, D.; Rieder, G., On the reliability of amorphous chalcogenide switching devices, J. Non-Cryst. Solids 29 (1978) 397-407.	
	CE5	Sharma, A.K.; Singh, B., Electrical conductivity measurements of evaporated selenium films in vacuum, Proc. Indian Natn. Sci. Acad. 46, A, (1980) 362-368.	
	CF5	Sharma, P., Structural, electrical and optical properties of silver selenide films, Ind. J. Of pure and applied phys. 35 (1997) 424-427.	
AT	CG5	Snell, A.J.; Lecomber, P.G.; Hajto, J.; Rose, M.J.; Owen, A.E.; Osborne, I.L., Analogue memory effects in metal/a-Si:H/metal memory devices, J. Non-Cryst. Solids 137-138 (1991) 1257-1262.	
	CH5	Snell, A.J.; Hajto, J.; Rose, M.J.; Osborne, L.S.; Holmes, A.; Owen, A.E.; Gibson, R.A.G., Analogue memory effects in metal/a-Si:H/metal thin film structures, Mat. Res. Soc. Symp. Proc. V 297, 1993, 1017-1021.	
	CI5	Stevenson, A.G., Microfilaments in amorphous chalcogenide memory devices, J. Phys. D: Appl. Phys. 8 (1975) L120-L122.	
	CJ5	Stevenson, A.G., The switching mechanisms in amorphous chalcogenide memory devices, J. Non-Cryst. Solids 21 (1976) 319-329.	
AT	CK5	Stocker, H.J., Bulk and thin film switching and memory effects in semiconducting chalcogenide glasses, App. Phys. Lett. 15 (1969) 55-57.	

M. TRAN

11/14/03



PTO/SB/08B (10-01)

Approved for use through 10/31/2002.OMB 0651-0031

U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO		Complete If Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/076,486		
		Filing Date	February 19, 2002		
		First Named Inventor	Stephen L. Casper		
		Group Art Unit	2818		
		Examiner Name	Not Known		
Sheet	8	of	8	Attorney Docket Number	M4065.0479/P479

CL5	Tanaka, K., Ionic and mixed conductions in Ag photodoping process, Mod. Phys. Lett B 4 (1990) 1373-1377.
CM5	Tanaka, K.; Iizima, S.; Sugi, M.; Okada, Y.; Kikuchi, M., Thermal effects on switching phenomenon in chalcogenide amorphous semiconductors, Solid State Comm. 8 (1970) 387-389.
CN5	Thornburg, D.D., Memory switching in a Type I amorphous chalcogenide, J. Elect. Mat. 2 (1973) 3-15.
CO5	Thornburg, D.D., Memory switching in amorphous arsenic triselenide, J. Non-Cryst. Solids 11 (1972) 113-120.
CP5	Thornburg, D.D.; White, R.M., Electric field enhanced phase separation and memory switching in amorphous arsenic triselenide, Journal(?) (1972) 4609-4612.
CQ5	Tichy, L.; Ticha, H., Remark on the glass-forming ability in GexSe1-x and AsxSe1-x systems, J. Non-Cryst. Solids 261 (2000) 277-281.
CR5	Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, Phys. Rev. B 48 (1993) 14650-14652.
CS5	Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, 9-13 September 1985.
CT5	Tregouet, Y.; Bernede, J.C., Silver movements in Ag2Te thin films: switching and memory effects, Thin Solid Films 57 (1979) 49-54.
CU5	Uemura, O.; Kameda, Y.; Kokai, S.; Satow, T., Thermally induced crystallization of amorphous Ge0.4Se0.6, J. Non-Cryst. Solids 117-118 (1990) 219-221.
CV5	Uttech, R.; Stevenson, H.; Sie, C.H.; Griener, J.D.; Raghavan, K.S., Electric field induced filament formation in As-Te-Ge glass, J. Non-Cryst. Solids 2 (1970) 358-370.
CD5	Viger, C.; Lefrancois, G.; Fleury, G., Anomalous behaviour of amorphous selenium films, J. Non-Cryst. Solids 33 (1976) 267-272.
CX5	Vodenicharov, C.; Parvanov, S.; Petkov, P., Electrode-limited currents in the thin-film M-GeSe-M system, Mat. Chem. And Phys. 21 (1989) 447-454.
CY5	Wang, S.-J.; Misium, G.R.; Camp, J.C.; Chen, K.-L.; Tigelaar, H.L., High-performance Metal/silicide antifuse, IEEE electron dev. Lett. 13 (1992) 471-472.
CZ5	Weirauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73.
CA6	West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the Ag As0.24S0.36Ag0.40 Ag System prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974.
CB6	West, W.C., Electrically erasable non-volatile memory via electrochemical deposition of multifractal aggregates, Ph.D. Dissertation, ASU 1998.
CC6	Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, Tg, with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the slope dTg/d<m> at the rigidity percolation threshold (<m>=2.4), J. Non-Cryst. Solids 151 (1992) 149-154.

Examiner Signature	<i>M. TRAN</i>	Date Considered	11/14/03
--------------------	----------------	-----------------	----------

*EXAMINER. Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*Applicant's unique citation designation number (optional). *Applicant is to place a check mark here if English language Translation is attached.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.



Substitute for form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/076,486
		Filing Date	February 19, 2002
		First Named Inventor	Stephen L. Casper
		Art Unit	2818
		Examiner Name	Not Yet Assigned
Sheet 1 of 1	Attorney Docket Number	M4065.0479/P479	

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
05	AA	5,761,115	06/1998	Kozicki et al.	365 / 182
	AB	5,896,312	04/1999	Kozicki et al.	365 / 153
	AC	5,914,893	06/1999	Kozicki et al.	365 / 107
	AD	6,084,796	07/2000	Kozicki et al.	365 / 153
	AE	5,883,827	03/1999	Morgan	365 / 100

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)			

* Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²

Examiner Signature	<i>U. J. K. A. N.</i>	Date Considered	11/14/03
-----------------------	-----------------------	--------------------	----------

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

* Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached